ABSTRACT OF THE DISCLOSURE

Processes are disclosed which facilitate improved high-density memory circuitry, most preferably dynamic random access memory (DRAM) circuitry. A semiconductor memory device includes i) a total of no more than 68,000,000 functional and operably addressable memory cells arranged in multiple memory arrays formed on a semiconductor die; and ii) circuitry formed on the semiconductor die permitting data to be written to and read from one or more of the memory cells, at least one of the memory arrays containing at least 100 square microns of continuous die surface area having at least 128 of the functional and operably addressable memory cells, more preferably, at least 100 square microns of continuous die surface area having at least 170 of the functional and operably addressable memory cells.

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